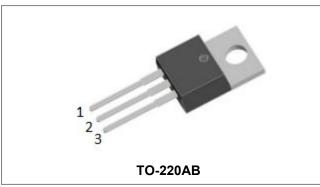






# **SBR60100CT SCHOTTKY RECTIFIER**



#### **Features**

- 200°C T<sub>J</sub> operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced
- · mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### **Circuit Diagram**



#### **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

### **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	100	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @Tc=133°C, rectangular wave form	30(Per Leg) 60(Per Device)	Α
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I <sub>FSM</sub>	8.3ms, Half Sine pulse, T <sub>C</sub> = 25 °C	400	Α

#### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop(Per Leg)*	V <sub>F1</sub>	@30A, Pulse, T <sub>J</sub> = 25 °C	0.83	0.90	V
	V <sub>F2</sub>	@30A, Pulse, T <sub>J</sub> = 125 °C	0.76	0.80	V
Reverse Current(Per Leg)*	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 25 °C	0.006	1.0	mA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 125 °C	0.1	20	mA
Junction Capacitance(Per Leg)	Ст	$@V_R = 5V, T_C = 25  ^{\circ}C, f_{SIG} = 1MHz$	400	800	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

<sup>\*</sup> Pulse width < 300 µs, duty cycle < 2%



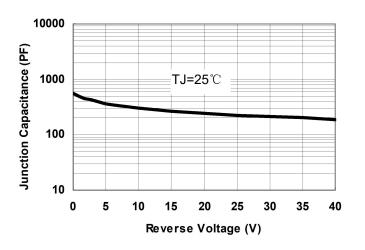




# **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +200	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +200	°C
Typical Thermal Resistance Junction to Case(Per Leg)	R <sub>0</sub> JC	DC operation	3	°C/W
Approximate Weight	wt	-	2	g

# **Ratings and Characteristics Curves**



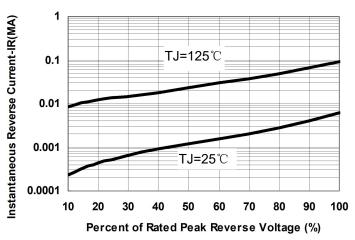


Fig.1-Typical Junction Capacitance

Fig.2-Typical Reverse Characteristics

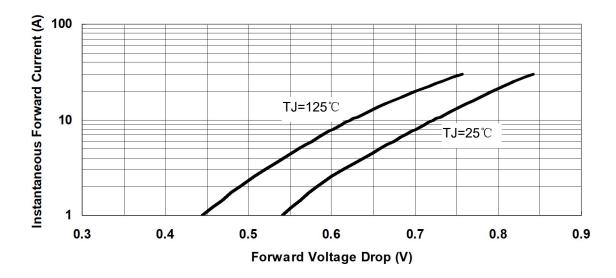


Fig.3-Typical Instantaneous Forward Voltage Characteristics

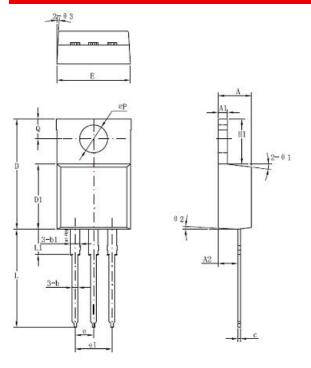
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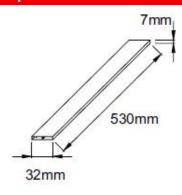


#### **Mechanical Dimensions TO-220AB**

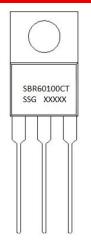


	Dimensions in			
Symbol	millimeters			
	Min	Typical	Max	
Α	4.42	4.57	4.72	
A1	1.17	1.27	1.37	
A2	2.52	2.69	2.89	
b	0.71	0.81	0.96	
b1	1.17	1.27	1.37	
С	0.31	0.38	0.61	
D	14.94	15.24	15.54	
D1	8.85	9.00	9.15	
E	10.01	10.16	10.31	
е		2.54		
e1	4.98	5.06	5.18	
H1	6.04	6.24	6.44	
L	12.7	13.56	13.80	
L1	3.56	3.5	3.96	
ФР	3.74	3.84	4.04	
Q	2.54	2.74	2.94	
Θ1		7°		
Θ2		3°		
Θ3		4°		

# **Tube Specification**



# **Marking Diagram**



Where XXXXX is YYWWL

SBR = Device Type 60 = Forward Current (60A) 100 = Reverse Voltage(100V) CT = Configuration

CT = Configuration
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

### **Ordering Information**

Device	Package	Shipping	
SBR60100CT	TO-220AB (Pb-Free)	50 pcs/ tube	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

- China Germany Korea Singapore United States
  - http://www.smc-diodes.com sales@ smc-diodes.com •







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